



THE DATASHEET OF ZTX749



ZTX749

PNP SILICON PLANAR MEDIUM POWER TRANSISTOR

ISSUE 1 – APRIL 94

FEATURES

- * 25 Volt V_{CE0}
- * 2 Amp continuous current
- * Low saturation voltage

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Transition Frequency	f_T	100	160		MHz	$I_C = 100\text{mA}$, $V_{CE} = 5\text{V}$ $f = 100\text{MHz}$
Output Capacitance	C_{obo}		55	100	pF	$V_{CB} = 10\text{V}$ $f = 1\text{MHz}$
Switching Times	t_{on}		40		ns	$I_C = 500\text{mA}$, $V_{CC} = 10\text{V}$
	t_{off}		450		ns	$I_B = I_{B2} = 50\text{mA}$

* Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	MAX.	UNIT
Thermal Resistance: Junction to Ambient ₁	$R_{Th(j-amb)1}$	175	$^\circ\text{C/W}$
Junction to Ambient ₂	$R_{Th(j-amb)2}$	116	$^\circ\text{C/W}$
Junction to Case	$R_{Th(j-case)}$	70	$^\circ\text{C/W}$

† Device mounted on P.C.B. with copper equal to 1 sq. Inch minimum.

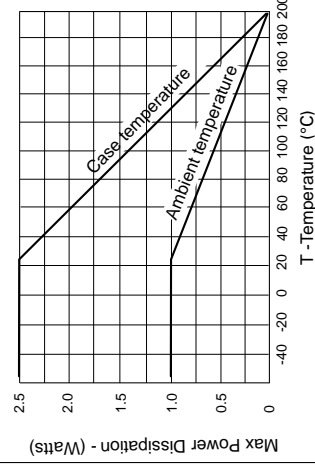
ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	UNIT
Collector-Base Voltage	V_{CB}	V
Collector-Emitter Voltage	V_{CE}	V
Emitter-Base Voltage	V_{EB}	V
Peak Pulse Current	I_{CP}	A
Continuous Collector Current	I_C	A
Power Dissipation at $T_{amb} = 25^\circ\text{C}$ derate above 25°C	P_D	W
Operating and Storage Temperature	T_{OS}	$^\circ\text{C}$

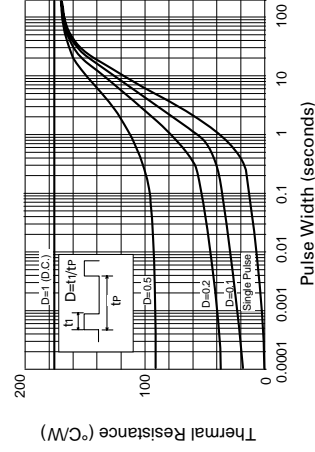
ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	UNIT
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-3
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-2
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5
Collector Cut-Off Current	I_{CBO}	μA
Emitter Cut-Off Current	I_{EBO}	μA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	V
Base-Emitter Turn-On Voltage	$V_{BE(on)}$	V
Static Forward Current Transfer Ratio	h_{FE}	70 10 75 15

* Measured under pulsed conditions. Pulse



Derating curve



Maximum transient thermal impedance

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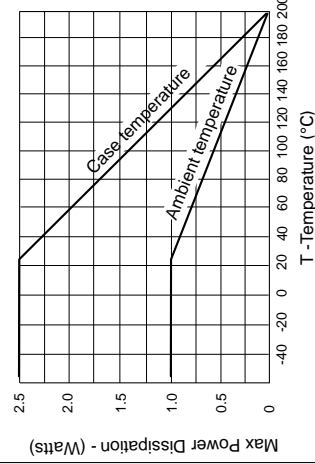
ABSOLUTE MAXIMUM RATINGS

PARAMETER
Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Peak Pulse Current
Continuous Collector Current
Power Dissipation at $T_{amb} = 25^\circ\text{C}$ derate above 25°C
Operating and Storage Temperature Range

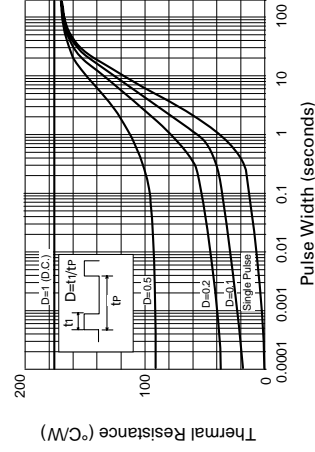
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PARAMETER	SYMBOL	MIN
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Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-2
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5
Collector Cut-Off Current	I_{CBO}	
Emitter Cut-Off Current	I_{EBO}	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	
Base-Emitter Turn-On Voltage	$V_{BE(on)}$	
Static Forward Current Transfer Ratio	h_{FE}	70 10 75 15

* Measured under pulsed conditions. Pulse



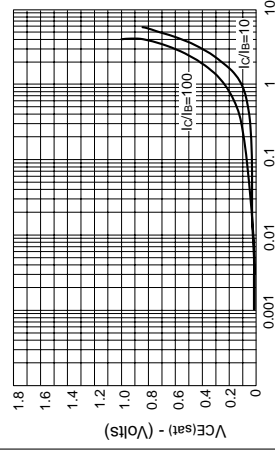
Derating curve



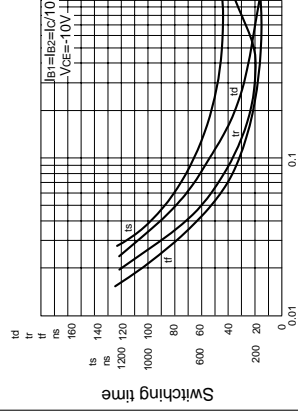
Maximum transient thermal impedance

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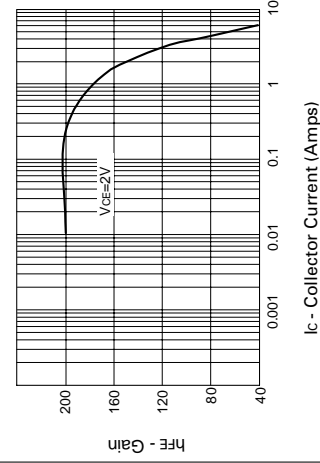
TYPICAL CHARACTERISTICS



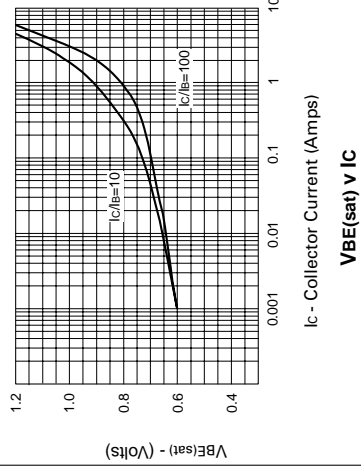
I_C - Collector Current (Amps)
 $V_{CE(sat)}$ v I_C



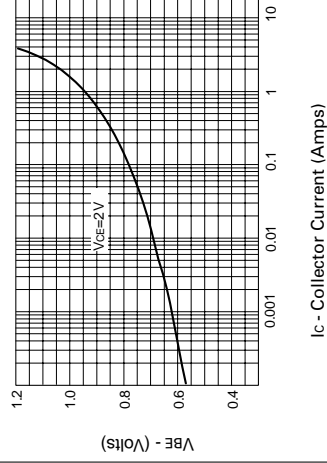
I_C - Collector Current (Amps)
Switching Speeds



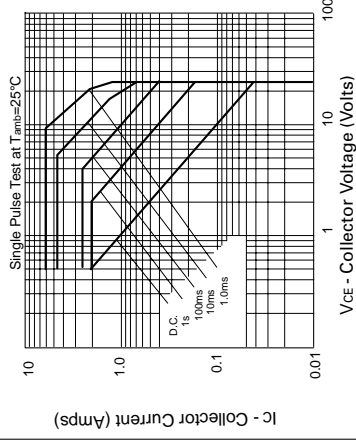
I_C - Collector Current (Amps)
 h_{FE} v I_C



I_C - Collector Current (Amps)
 $V_{BE(sat)}$ v I_C





I_C - Collector Current (Amps)
 $V_{BE(on)}$ v I_C



Safe Operating Area

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-  Obsolete Management
-  Cost Control Management
-  Shortage Management
-  Alternative Solution
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